

Cornelis De Groot

List of Publications by Year in descending order

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papers

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172207

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201
all docs

201
docs citations

201
times ranked

3997
citing authors

#	ARTICLE	IF	CITATIONS
1	Electrodeposited WS ₂ monolayers on patterned graphene. 2D Materials, 2022, 9, 015025.	2.0	3
2	VO ₂ metasurface smart thermal emitter with high visual transparency for passive radiative cooling regulation in space and terrestrial applications. Nanophotonics, 2022, 11, 4101-4114.	2.9	37
3	Inverse design of structural color: finding multiple solutions <i>via</i> conditional generative adversarial networks. Nanophotonics, 2022, 11, 3057-3069.	2.9	14
4	Back-End-of-Line SiC-Based Memristor for Resistive Memory and Artificial Synapse. Advanced Electronic Materials, 2022, 8, .	2.6	16
5	Wafer-Scale 200 mm Metal Oxide Infrared Metasurface with Tailored Differential Emissivity Response in the Atmospheric Windows. Advanced Optical Materials, 2022, 10, .	3.6	6
6	Tungsten disulfide thin films via electrodeposition from a single source precursor. Chemical Communications, 2021, 57, 10194-10197.	2.2	3
7	Direct observation of surface charge redistribution in active nanoscale conducting channels by Kelvin Probe Force Microscopy. Nanotechnology, 2021, 32, 325206.	1.3	2
8	Lateral Growth of MoS ₂ 2D Material Semiconductors Over an Insulator Via Electrodeposition. Advanced Electronic Materials, 2021, 7, 2100419.	2.6	6
9	Single-nanoantenna driven nanoscale control of the VO ₂ insulator to metal transition. Nanophotonics, 2021, 10, 3745-3758.	2.9	4
10	Phase-Change Memory by GeSbTe Electrodeposition in Crossbar Arrays. ACS Applied Electronic Materials, 2021, 3, 3610-3618.	2.0	12
11	The Effects of Hydrogen Annealing on Carbon Nanotube Field-Effect Transistors. Nanomaterials, 2021, 11, 2481.	1.9	0
12	Low temperature CVD of thermoelectric SnTe thin films from the single source precursor, [ⁿ Bu ₃ Sn(Te ⁿ Bu)]. Dalton Transactions, 2021, 50, 998-1006.	1.6	7
13	Low-Pressure CVD of GeE (E = Te, Se, S) Thin Films from Alkylgermanium Chalcogenolate Precursors and Effect of Deposition Temperature on the Thermoelectric Performance of GeTe. ACS Applied Materials & Interfaces, 2021, 13, 47773-47783.	4.0	7
14	A Novel Selective Carrier Modulation Technique to Form a Planar Metal Oxide Metasurface. , 2021, , .		0
15	Electrodeposition of GeSbTe-Based Resistive Switching Memory in Crossbar Arrays. Journal of Physical Chemistry C, 2021, 125, 26247-26255.	1.5	9
16	Optical Modulation in a Si Microring Resonator Inspired by Biological Classical Conditioning. , 2021, , .		0
17	Mathematical model and optimization of a thin-film thermoelectric generator. JPhys Energy, 2020, 2, 014001.	2.3	8
18	Large-Area Electrodeposition of Few-Layer MoS ₂ on Graphene for 2D Material Heterostructures. ACS Applied Materials & Interfaces, 2020, 12, 49786-49794.	4.0	21

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19	Thermoelectric Properties of Bismuth Telluride Thin Films Electrodeposited from a Nonaqueous Solution. <i>ACS Omega</i> , 2020, 5, 14679-14688.	1.6	16
20	Improved thermoelectric performance of Bi ₂ Se ₃ alloyed Bi ₂ Te ₃ thin films via low pressure chemical vapour deposition. <i>Journal of Alloys and Compounds</i> , 2020, 848, 156523.	2.8	10
21	Modelling resistive and phase-change memory with passive selector arrays: a MATLAB tool. <i>Journal of Computational Electronics</i> , 2020, 19, 1203-1214.	1.3	5
22	Embedded Metal Oxide Plasmonics Using Local Plasma Oxidation of AZO for Planar Metasurfaces. <i>Advanced Materials</i> , 2020, 32, e2001534.	11.1	18
23	Selective Chemical Vapor Deposition Approach for Sb ₂ Te ₃ Thin Film Micro-thermoelectric Generators. <i>ACS Applied Energy Materials</i> , 2020, 3, 5840-5846.	2.5	9
24	Electrodeposition of MoS ₂ from Dichloromethane. <i>Journal of the Electrochemical Society</i> , 2020, 167, 106511.	1.3	16
25	Metal Oxide Meta-Optical Solar Reflectors for Space Applications. , 2020, , .		0
26	Towards a 3D GeSbTe phase change memory with integrated selector by non-aqueous electrodeposition. <i>Faraday Discussions</i> , 2019, 213, 339-355.	1.6	14
27	Reviewâ€”Beyond the Highs and Lows: A Perspective on the Future of Dielectrics Research for Nanoelectronic Devices. <i>ECS Journal of Solid State Science and Technology</i> , 2019, 8, N159-N185.	0.9	17
28	[Ge(Te ⁿ Bu) ₄] â€” a single source precursor for the chemical vapour deposition of germanium telluride thin films. <i>Dalton Transactions</i> , 2019, 48, 117-124.	1.6	7
29	Multibeam Dual-Circularly Polarized Reflectarray for Connected and Autonomous Vehicles. <i>IEEE Transactions on Vehicular Technology</i> , 2019, 68, 3574-3585.	3.9	25
30	Electrodeposition of bismuth telluride from a weakly coordinating, non-aqueous solution. <i>Journal of Electroanalytical Chemistry</i> , 2019, 839, 134-140.	1.9	7
31	Behavior of Gold-Doped Silicon Substrate under Small- and Large-RF Signal. , 2019, , .		1
32	Conductive-bridge memory cells based on a nanoporous electrodeposited GeSbTe alloy. <i>Nanotechnology</i> , 2019, 30, 025202.	1.3	12
33	Total Ionizing Dose Hardened and Mitigation Strategies in Deep Submicrometer CMOS and Beyond. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 808-819.	1.6	17
34	VO ₂ Thermochromic Metamaterial-Based Smart Optical Solar Reflector. <i>ACS Photonics</i> , 2018, 5, 2280-2286.	3.2	161
35	Metasurface Optical Solar Reflectors Using AZO Transparent Conducting Oxides for Radiative Cooling of Spacecraft. <i>ACS Photonics</i> , 2018, 5, 495-501.	3.2	114
36	Electrodeposition of Crystalline HgTe from a Non-Aqueous Plating Bath. <i>Journal of the Electrochemical Society</i> , 2018, 165, D802-D807.	1.3	5

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37	Back-end-of-line a-SiO _x Cy:H dielectrics for resistive memory. AIP Advances, 2018, 8, .	0.6	10
38	Electrodeposition of a Functional Solid State Memory Material: Germanium Antimony Telluride from a Non-Aqueous Plating Bath. Journal of the Electrochemical Society, 2018, 165, D557-D567.	1.3	9
39	Combinatorial synthesis and screening of (Ba,Sr)(Ti,Mn)O ₃ thin films for optimization of tunable co-planar waveguides. Journal of Materials Chemistry C, 2018, 6, 6222-6228.	2.7	9
40	Compositionally tunable ternary Bi ₂ (Se ^x Te ^x) ₃ and (Bi _{1-y} Sb _y) ₂ Te ₃ thin films <i>via</i> low pressure chemical vapour deposition. Journal of Materials Chemistry C, 2018, 6, 7734-7739.	2.7	15
41	Selection by current compliance of negative and positive bipolar resistive switching behaviour in ZrO ₂ /ZrO ₂ bilayer memory. Journal Physics D: Applied Physics, 2017, 50, 175101.	1.3	21
42	Total Ionizing Dose, Random Dopant Fluctuations, and its combined effect in the 45nm PDSOI node. Microelectronics Reliability, 2017, 68, 21-29.	0.9	11
43	Amorphous SiC resistive memory with embedded Cu nanoparticles. Microelectronic Engineering, 2017, 174, 1-5.	1.1	4
44	Active counter electrode in a-SiC electrochemical metallization memory. Journal Physics D: Applied Physics, 2017, 50, 325102.	1.3	6
45	A systematic method for simulating total ionizing dose effects using the finite elements method. Journal of Computational Electronics, 2017, 16, 548-555.	1.3	7
46	Compliance-Free ZrO ₂ /ZrO ₂ /ZrO ₂ Resistive Memory with Controllable Interfacial Multistate Switching Behaviour. Nanoscale Research Letters, 2017, 12, 384.	3.1	31
47	Three-dimensional Finite Elements Method simulation of Total Ionizing Dose in 22 nm bulk nFinFETs. Nuclear Instruments & Methods in Physics Research B, 2017, 393, 39-43.	0.6	6
48	Metal oxide metasurfaces for active control and space technology. , 2017, , .		0
49	Total dose radiation hardening of MOS transistors by fluorine implantation. , 2017, , .		0
50	Nanoscale modeling of electro-plasmonic tunable devices for modulators and metasurfaces. Optics Express, 2017, 25, 10031.	1.7	9
51	Fermi Level Tuning of ZnO Films Through Supercycled Atomic Layer Deposition. Nanoscale Research Letters, 2017, 12, 541.	3.1	15
52	Electrically tunable gap-loaded plasmonic nanostructures. , 2017, , .		0
53	Switching mechanisms of Cu/SiC resistive memories with W and Au counter electrodes. , 2016, , .		0
54	Tuning the linear and non-linear optical response of orthogonal dimmer antennas for metasurfaces. , 2016, , .		0

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55	Forming-free resistive switching of tunable ZnO films grown by atomic layer deposition. <i>Microelectronic Engineering</i> , 2016, 161, 7-12.	1.1	26
56	Antenna-assisted picosecond control of nanoscale phase transition in vanadium dioxide. <i>Light: Science and Applications</i> , 2016, 5, e16173-e16173.	7.7	87
57	Composition-modulated electrodeposited PdNi-Si hydrogen sensors for low power applications. , 2016, , .		0
58	Nanoscale arrays of antimony telluride single crystals by selective chemical vapor deposition. <i>Scientific Reports</i> , 2016, 6, 27593.	1.6	15
59	Microstructure and electrical properties of co-sputtered Cu embedded amorphous SiC. <i>Materials Letters</i> , 2016, 178, 60-63.	1.3	4
60	Drain current multiplication in thin pillar vertical MOSFETs due to depletion isolation and charge coupling. <i>Journal of Computational Electronics</i> , 2016, 15, 839-849.	1.3	0
61	Ultrafast control of plasmonic nanoantennas driven by hot-spot induced phase-transitions in VO ₂ . , 2016, , .		0
62	Switching kinetics of SiC resistive memory for harsh environments. <i>AIP Advances</i> , 2015, 5, 077121.	0.6	19
63	Electron beam lithography tri-layer lift-off to create ultracompact metal/metal oxide 2D patterns on CaF ₂ substrate for surface-enhanced infrared spectroscopy. <i>Microelectronic Engineering</i> , 2015, 141, 87-91.	1.1	7
64	New plasmonic materials and fabrication tools for near- and mid-infrared sensing and spectroscopy. , 2015, , .		3
65	Total Ionizing Dose and random dopant fluctuation effects in 65-nm gate length partially depleted Silicon-on-Insulator nMOSFETs. , 2015, , .		0
66	Quantification of misalignment in e-beam lithography due to height map error on optically non-uniform substrates for plasmonic nanoantennas. , 2015, , .		0
67	Non-aqueous electrodeposition of functional semiconducting metal chalcogenides: Ge ₂ Sb ₂ Te ₅ phase change memory. <i>Materials Horizons</i> , 2015, 2, 420-426.	6.4	28
68	Extreme Subwavelength Metal Oxide Direct and Complementary Metamaterials. <i>ACS Photonics</i> , 2015, 2, 606-614.	3.2	33
69	Tailoring Second-Harmonic Generation in Single L-Shaped Plasmonic Nanoantennas from the Capacitive to Conductive Coupling Regime. <i>ACS Photonics</i> , 2015, 2, 1592-1601.	3.2	49
70	Phase-Change Memory Properties of Electrodeposited Ge-Sb-Te Thin Film. <i>Nanoscale Research Letters</i> , 2015, 10, 432.	3.1	12
71	Chemical vapour deposition of antimony chalcogenides with positional and orientational control: precursor design and substrate selectivity. <i>Journal of Materials Chemistry C</i> , 2015, 3, 423-430.	2.7	46
72	Using Mobile Technologies to Co-Construct TPACK in Teacher Education. <i>Advances in Higher Education and Professional Development Book Series</i> , 2015, , 195-219.	0.1	1

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73	Total Dose Hardness of $\frac{\text{HfO}_x/\text{TiN}}{\text{TiN}}$ Resistive Random Access Memory. IEEE Transactions on Nuclear Science, 2014, 61, 2991-2996.	1.2	11
74	Contact resistance measurement of $\text{Ge}_2\text{Sb}_2\text{Te}_5$ phase change material to TiN electrode by spacer etched nanowire. Semiconductor Science and Technology, 2014, 29, 095003.	1.0	17
75	Ultrafine control of partially loaded single plasmonic nanoantennas fabricated using e-beam lithography and helium ion beam milling. , 2014, , .		1
76	Nonpolar resistive switching in Cu/SiC/Au non-volatile resistive memory devices. Applied Physics Letters, 2014, 104, .	1.5	46
77	Plasmonics and Metamaterials with Transparent Conducting Oxides. ECS Transactions, 2014, 64, 291-298.	0.3	3
78	Effect of Stoichiometry of TiN Electrode on the Switching Behavior of TiN/HfO _x /TiN Structures for Resistive RAM. Materials Research Society Symposia Proceedings, 2014, 1631, 1.	0.1	3
79	Analytical and numerical model of spiral inductors on high resistivity silicon substrates. Solid-State Electronics, 2014, 93, 43-48.	0.8	8
80	The effect of atomic layer deposition temperature on switching properties of HfO _x resistive RAM devices. , 2014, , .		4
81	Total ionizing dose response of fluorine implanted Silicon-On-Insulator buried oxide. Microelectronics Reliability, 2014, 54, 2339-2343.	0.9	8
82	Low loss 67-GHz coplanar waveguides and spiral inductors on 100 kΩ/cm gold-doped high resistivity Cz-Silicon. , 2014, , .		1
83	Surface-Enhanced Infrared Spectroscopy Using Metal Oxide Plasmonic Antenna Arrays. Nano Letters, 2014, 14, 346-352.	4.5	175
84	Hotspot-mediated ultrafast nonlinear control of multifrequency plasmonic nanoantennas. Nature Communications, 2014, 5, 4869.	5.8	75
85	Optimal Polarization Conversion in Coupled Dimer Plasmonic Nanoantennas for Metasurfaces. ACS Nano, 2014, 8, 6390-6399.	7.3	81
86	Resistive switching of Cu/SiC/Au memory devices with a high ON/OFF ratio. Solid-State Electronics, 2014, 94, 98-102.	0.8	27
87	Controlling the nanostructure of bismuth telluride by selective chemical vapour deposition from a single source precursor. Journal of Materials Chemistry A, 2014, 2, 4865.	5.2	31
88	Amorphous SiC based non-volatile resistive memories with ultrahigh ON/OFF ratios. Microelectronic Engineering, 2014, 119, 61-64.	1.1	20
89	Surface-Enhanced Infrared Spectroscopy using ultra-compact indium tin oxide (ITO) sensor arrays. , 2014, , .		1
90	Ultrafast Nonlinear Control of Progressively Loaded, Single Plasmonic Nanoantennas Fabricated Using Helium Ion Milling. Nano Letters, 2013, 13, 5647-5653.	4.5	76

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91	Area Selective Growth of Titanium Diselenide Thin Films into Micropatterned Substrates by Low-Pressure Chemical Vapor Deposition. <i>Chemistry of Materials</i> , 2013, 25, 4719-4724.	3.2	29
92	Non-aqueous electrodeposition of p-block metals and metalloids from halometallate salts. <i>RSC Advances</i> , 2013, 3, 15645.	1.7	43
93	Telluroether and Selenoether Complexes as Single Source Reagents for Low Pressure Chemical Vapor Deposition of Crystalline Ga ₂ Te ₃ and Ga ₂ Se ₃ Thin Films. <i>Chemistry of Materials</i> , 2013, 25, 1829-1836.	3.2	37
94	A novel top-down fabrication process for Ge ₂ Sb ₂ Te ₅ phase change material nanowires. , 2013, , .		0
95	Coplanar waveguides on gold-doped high resistivity silicon for 67-GHz microwave application. , 2013, , .		1
96	Low Pressure Chemical Vapour Deposition of Crystalline Ga ₂ Te ₃ and Ga ₂ Se ₃ Thin Films from Single Source Precursors Using Telluroether and Selenoether Complexes. <i>Physics Procedia</i> , 2013, 46, 142-148.	1.2	6
97	Effect of interfacial PdNi concentration on time response of Si-based electrodeposited hydrogen sensors. , 2013, , .		0
98	Electrical transport properties of isolated carbon nanotube/Si heterojunction Schottky diodes. <i>Applied Physics Letters</i> , 2013, 103, 193111.	1.5	12
99	Helium ion beam milling to create a nano-structured domain wall magnetoresistance spin valve. <i>Nanotechnology</i> , 2012, 23, 395302.	1.3	18
100	CMOS Compatible Growth of Carbon Nanotubes and Their Application in Field-Effect Transistors. <i>Materials Research Society Symposia Proceedings</i> , 2012, 1407, 74.	0.1	0
101	Electro-Deposited PdNi-Si Schottky Barrier Hydrogen Sensors with Improved Time Response. <i>Procedia Engineering</i> , 2012, 47, 37-40.	1.2	1
102	Low power hydrogen sensors using electrodeposited PdNi-Si Schottky diodes. <i>Sensors and Actuators B: Chemical</i> , 2012, 170, 176-181.	4.0	12
103	Highly Selective Chemical Vapor Deposition of Tin Diselenide Thin Films onto Patterned Substrates via Single Source Diselenoether Precursors. <i>Chemistry of Materials</i> , 2012, 24, 4442-4449.	3.2	64
104	Interference, Coupling, and Nonlinear Control of High-Order Modes in Single Asymmetric Nanoantennas. <i>ACS Nano</i> , 2012, 6, 6462-6470.	7.3	46
105	Improved Drive Current in RF Vertical MOSFETS Using Hydrogen Anneal. <i>IEEE Electron Device Letters</i> , 2011, 32, 279-281.	2.2	1
106	Gold-doped high resistivity Czochralski-silicon for integrated passive devices and 3D integration. , 2011, , .		1
107	Single domain wall magnetoresistance electron-beam fabrication and magnetoresistance measurement. <i>Proceedings of SPIE</i> , 2011, , .	0.8	1
108	Fabrication of low loss coplanar waveguides on gold-doped Czochralski-silicon. <i>Proceedings of SPIE</i> , 2011, , .	0.8	0

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109	The electrodeposition, magnetic and electrical characterisation of Palladium–Nickel alloys. Journal of Electroanalytical Chemistry, 2011, 655, 87-91.	1.9	3
110	On the mechanism of carbon nanotube formation: the role of the catalyst. Journal of Physics Condensed Matter, 2011, 23, 394201.	0.7	13
111	Reduced microwave attenuation in coplanar waveguides using deep level impurity compensated Czochralski-silicon substrates. Semiconductor Science and Technology, 2011, 26, 072001.	1.0	9
112	Metal-Catalyst-Free Growth of Carbon Nanotubes and Their Application in Field-Effect Transistors. Electrochemical and Solid-State Letters, 2011, 14, K21.	2.2	5
113	Our Quest for Mutualism in University–School Partnerships. Educational Forum, 2010, 74, 306-317.	0.9	9
114	Low power hydrogen sensors using electrodeposited PdNi–Si schottky diodes. Procedia Engineering, 2010, 5, 143-146.	1.2	4
115	Self-Aligned Silicidation of Surround Gate Vertical MOSFETs for Low Cost RF Applications. IEEE Transactions on Electron Devices, 2010, 57, 3318-3326.	1.6	3
116	Fabrication and simulation of nanostructures for domain wall magnetoresistance studies on nickel. Journal of Magnetism and Magnetic Materials, 2010, 322, 1467-1470.	1.0	8
117	Electrodeposited PdNi as possible ferromagnetic contacts for carbon nanotubes. Physica Status Solidi (B): Basic Research, 2010, 247, 888-891.	0.7	5
118	Chemical Vapour Deposition of CNTs Using Structural Nanoparticle Catalysts. , 2010, , .		0
119	Spin transport in germanium at room temperature. Applied Physics Letters, 2010, 97, 162104.	1.5	43
120	Growth of Carbon Nanotubes on HfO ₂ towards Highly Sensitive Nano-Sensors. Japanese Journal of Applied Physics, 2010, 49, 04DN11.	0.8	2
121	Magnetoresistance in a lithography defined single constrained domain wall spin-valve. Applied Physics Letters, 2010, 97, 262501.	1.5	9
122	Electrodeposited Ni/Ge contacts for limiting leakage currents in Schottky barrier MOSFETs. , 2009, , .		1
123	Fabrication of plasmonic Au nano-void trench arrays by guided self-assembly. , 2009, , .		0
124	The fabrication of plasmonic Au nanovoid trench arrays by guided self-assembly. Nanotechnology, 2009, 20, 285309.	1.3	13
125	Growth of Single-Walled Carbon Nanotubes Using Germanium Nanocrystals Formed by Implantation. Journal of the Electrochemical Society, 2009, 156, K144.	1.3	17
126	A vertical transport geometry for electrical spin injection and extraction in Si. Solid State Communications, 2009, 149, 1565-1568.	0.9	1

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127	Inhomogeneous Ni/Ge Schottky barriers due to variation in Fermi-level pinning. <i>Microelectronic Engineering</i> , 2009, 86, 1599-1602.	1.1	12
128	Fe/Ge catalyzed carbon nanotube growth on HfO ₂ for nano-sensor applications. , 2009, , .		0
129	Observation of Negative Differential Conductance in a Reverse-Biased Ni/Ge Schottky Diode. <i>IEEE Electron Device Letters</i> , 2009, 30, 966-968.	2.2	6
130	Thermionic field emission at electrodeposited Ni ⁶¹ Si Schottky barriers. <i>Solid-State Electronics</i> , 2008, 52, 1032-1038.	0.8	52
131	High-quality NiGe/Ge diodes for Schottky barrier MOSFETs. <i>Materials Science in Semiconductor Processing</i> , 2008, 11, 305-309.	1.9	8
132	Fabrication of Nano-Structured Gold Arrays by Guided Self-assembly for Plasmonics. <i>Materials Research Society Symposia Proceedings</i> , 2008, 1077, 40101.	0.1	0
133	Numerical investigation of domain walls in constrained geometries. <i>Journal of Applied Physics</i> , 2008, 103, 07D926.	1.1	4
134	Long range ordering in self-assembled Ni arrays on patterned Si. <i>Journal of Magnetism and Magnetic Materials</i> , 2007, 316, e78-e81.	1.0	6
135	Transport mechanisms at Ni-Si Schottky barriers for spin injection. , 2006, , .		0
136	The structural and electrical properties of thermally grown TiO ₂ thin films. <i>Journal of Physics Condensed Matter</i> , 2006, 18, 645-657.	0.7	47
137	Shallow junctions on pillar sidewalls for sub-100-nm vertical MOSFETs. <i>IEEE Electron Device Letters</i> , 2006, 27, 692-695.	2.2	22
138	Analysis of thermionic emission from electrodeposited Ni ⁶¹ Si Schottky barriers. <i>Solid State Communications</i> , 2006, 140, 508-513.	0.9	28
139	Depletion-isolation effect in vertical MOSFETs during the transition from partial to fully depleted operation. <i>IEEE Transactions on Electron Devices</i> , 2006, 53, 929-932.	1.6	7
140	Asymmetric gate-induced drain leakage and body leakage in vertical MOSFETs with reduced parasitic capacitance. <i>IEEE Transactions on Electron Devices</i> , 2006, 53, 1080-1087.	1.6	21
141	Anisotropy of Magnetization Reversal and Magnetoresistance in Square Arrays of Permalloy Nano-Rings. <i>IEEE Transactions on Magnetics</i> , 2006, 42, 2948-2950.	1.2	3
142	Orientation and symmetry control of inverse sphere magnetic nanoarrays by guided self-assembly. <i>Journal of Applied Physics</i> , 2006, 100, 113720.	1.1	17
143	Lysosomal Destabilization Contributes to Apoptosis of Germinal Center B-lymphocytes. <i>Journal of Histochemistry and Cytochemistry</i> , 2006, 54, 1425-1435.	1.3	38
144	Semi-insulating Czochralski-silicon for Radio Frequency Applications. , 2006, , .		2

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145	Ge-catalyzed Vapour-Liquid-Solid growth of Carbon Nanotubes. , 2006, , .		0
146	Enhancement of resistivity of Czochralski silicon by deep level manganese doping. Applied Physics Letters, 2006, 89, 112122.	1.5	12
147	The vertical metal insulator semiconductor tunnel transistor: A proposed Fowlerâ€œNordheim tunneling device. Microelectronic Engineering, 2005, 81, 171-180.	1.1	15
148	Shape-induced anisotropy in antidot arrays from self-assembled templates. IEEE Transactions on Magnetics, 2005, 41, 3598-3600.	1.2	4
149	Electrodeposition of Ni-Si Schottky barriers. IEEE Transactions on Magnetics, 2005, 41, 2639-2641.	1.2	26
150	Electrodeposition of Ni-Si Schottky barriers. , 2005, , .		0
151	Shape induced anisotropy in hybrid anti-dot arrays from guided self-assembly templates. , 2005, , .		0
152	Metal catalyst-free low-temperature carbon nanotube growth on SiGe islands. Applied Physics Letters, 2005, 86, 233110.	1.5	43
153	Design of 50-nm Vertical MOSFET Incorporating a Dielectric Pocket. IEEE Transactions on Electron Devices, 2004, 51, 158-160.	1.6	34
154	Recent developments in deca-nanometer vertical MOSFETs. Microelectronic Engineering, 2004, 72, 230-235.	1.1	11
155	Single, double and surround gate vertical MOSFETs with reduced parasitic capacitance. Solid-State Electronics, 2004, 48, 511-519.	0.8	50
156	Reduction of parasitic capacitance in vertical mosfets by spacer local oxidation. IEEE Transactions on Electron Devices, 2003, 50, 1487-1493.	1.6	32
157	Polycrystalline silicon-germanium emitters for gain control, with application to SiGe HBTs. IEEE Transactions on Electron Devices, 2003, 50, 1480-1486.	1.6	21
158	Proteinases and their inhibitors in the immune system. International Review of Cytology, 2003, 222, 197-236.	6.2	12
159	Application of Polycrystalline SiGe for Gain Control in SiGe Heterojunction Bipolar Transistors. , 2002, , .		1
160	Resonant tunnelling in Dy- or Gd-doped Al ₂ O ₃ magnetic tunnel junctions. Journal of Physics Condensed Matter, 2002, 14, 5153-5159.	0.7	3
161	A 50nm channel vertical MOSFET concept incorporating a retrograde channel and a dielectric pocket. , 2001, , .		2
162	Magnetic ordering of the R ₆ Fe ₁₃ Sn (R=Nd, Pr) compounds studied by neutron diffraction. Journal of Magnetism and Magnetic Materials, 2000, 218, 31-41.	1.0	11

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163	Gallium oxide as an insulating barrier for spin-dependent tunneling junctions. Applied Physics Letters, 2000, 77, 3630-3632.	1.5	113
164	Spin-polarized tunnelling, magnetoresistance and interfacial effects in ferromagnetic junctions. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 2000, 80, 195-206.	0.6	34
165	Magnetic ordering of Pr ₆ Fe ₁₃ Si and Nd ₆ Fe ₁₃ Au studied by neutron diffraction. Journal of Physics Condensed Matter, 1999, 11, 4469-4481.	0.7	14
166	Magnetoelastic anisotropy in NdFeB permanent magnets. Journal of Applied Physics, 1999, 85, 8312-8316.	1.1	21
167	Magnetic ordering of ErFe ₄ Ge ₂ studied by neutron diffraction and magnetic measurements. Journal of Magnetism and Magnetic Materials, 1999, 191, 261-276.	1.0	14
168	Low-temperature magnetisation and specific heat in antiferromagnetic rare-earth germanides of the type R ₃ Ge ₄ . Journal of Magnetism and Magnetic Materials, 1998, 177-181, 1147-1148.	1.0	3
169	Neutron diffraction and magnetization investigation of Tb ₂ Co ₁₇ â ^x Gax intermetallics. Journal of Magnetism and Magnetic Materials, 1998, 177-181, 1044-1045.	1.0	8
170	Structure and magnetic properties of Nd ₂ Co ₁₇ â ^x Gax compounds studied by magnetic measurements and neutron diffraction. Journal of Magnetism and Magnetic Materials, 1998, 189, 329-334.	1.0	8
171	Magnetic properties of Tb ₂ Co ₁₇ â ^x Gax compounds studied by magnetic measurements and neutron diffraction. Journal of Alloys and Compounds, 1998, 264, 76-81.	2.8	18
172	On the magnetic ordering of R ₆ Fe ₁₃ X compounds. Journal of Alloys and Compounds, 1998, 280, 44-55.	2.8	19
173	Two-powder Nd ₂ Fe ₁₄ B magnets with DyGa-addition. Journal of Applied Physics, 1998, 83, 388-393.	1.1	48
174	Time-of-Flight Neutron Powder Diffraction Investigation of Tb ₂ ₂/sub>Co_{17-x}/sub>Ga_x/sub>; Permanent Magnet Materials. Materials Science Forum, 1998, 278-281, 537-541.	0.3	1
175	Magnetic properties of R ₆ Fe ₁₃ â ^x M _{1+x} compounds and their hydrides. Physical Review B, 1998, 57, 11472-11482.	1.1	47
176	A Mössbauer spectral study of Nd ₆ Fe ₁₃ X, where X is Cu, Ag, and Au and of the spin reorientation in Nd ₆ Fe ₁₃ Si. Journal of Applied Physics, 1998, 83, 1554-1562.	1.1	20
177	A Mössbauer spectral study of the Nd ₆ Fe ₁₃ X compounds where X is Si, Cu, Ag, and Au. Journal of Applied Physics, 1997, 81, 5435-5437.	1.1	11
178	Magnetic properties of Tb ₂ Mn ₁₇ C _x compounds studied by magnetic measurements and neutron diffraction. Journal of Alloys and Compounds, 1997, 248, 121-124.	2.8	3
179	Structure and magnetic ordering in the defect compound ErGe _{1.83} . Journal of Alloys and Compounds, 1997, 252, 53-58.	2.8	25
180	Metamagnetic behaviour of La _{1-â^x} GdxFe ₁₂ B ₆ compounds. Journal of Alloys and Compounds, 1997, 256, 82-85.	2.8	23

#	ARTICLE	IF	CITATIONS
181	Magnetic properties of $\text{Pr}_2\text{Co}_{17-x}\text{Al}_x$ and $\text{Y}_2\text{Co}_{17-x}\text{Al}_x$. Journal of Alloys and Compounds, 1997, 259, 42-46.	2.8	16
182	Antiferromagnetic ordering in the novel Dy_3Ge_4 and $\text{DyGe}_{1.3}$ compounds studied by neutron diffraction and magnetic measurements. Journal of Alloys and Compounds, 1997, 262-263, 492-497.	2.8	12
183	Canted antiferromagnetic structure of the novel compound Er_3Ge_4 by neutron diffraction and magnetic measurements. Journal of Magnetism and Magnetic Materials, 1997, 169, 253-260.	1.0	15
184	Magnetic properties of $\text{R}_2\text{Co}_{17-x}\text{Al}_x$ compounds (R = Ho, Dy, Y). Physica B: Condensed Matter, 1997, 229, 213-216.	1.3	23
185	Crystallographic and magnetic structure of the novel compound $\text{ErGe}_{1.83}$. Physica B: Condensed Matter, 1997, 234-236, 652-653.	1.3	2
186	Magnetic properties and neutron diffraction of TbMn_4Al_8 . Journal of Alloys and Compounds, 1996, 232, 154-159.	2.8	14
187	The magnetic ordering of the novel compound ErGe_3 . Journal of Alloys and Compounds, 1996, 232, 165-168.	2.8	18
188	Magnetic and Mössbauer spectral properties of the compound $\text{Nd}_6\text{Fe}_{13}\text{Au}$. Journal of Alloys and Compounds, 1996, 233, 161-164.	2.8	20
189	Magnetic properties of $\text{Nd}_2\text{Co}_{17-x}\text{Al}_x$ compounds studied by magnetic measurements and neutron diffraction. Journal of Alloys and Compounds, 1996, 233, 188-191.	2.8	27
190	Note on the crystal structure and magnetic properties of the compounds $\text{Ce}_2\text{Ni}_{17}\text{Si}_9$ and $\text{Ce}_2\text{Co}_{17}\text{Si}_9$. Journal of Alloys and Compounds, 1996, 235, 62-65.	2.8	20
191	Crystal structure and magnetic properties of $\text{CeNi}_{11-x}\text{Six}$ compounds. Journal of Alloys and Compounds, 1996, 241, 124-126.	2.8	1
192	Erratum to "Magnetic and Mössbauer spectral properties of the compound $\text{Nd}_6\text{Fe}_{13}\text{Au}$ ". [J. Alloys Compd., 233 (1996) 161-164]. Journal of Alloys and Compounds, 1996, 245, 188.	2.8	3
193	Susceptibility of $(\text{Gd},\text{La})\text{Mn}_2(\text{Ge},\text{Si})_2$ compounds in the magnetically ordered regime. Journal of Magnetism and Magnetic Materials, 1996, 157-158, 639-640.	1.0	7
194	Re-entrant ferromagnetism in the $\text{ThFe}_3\text{-Al}$ system. Journal of Magnetism and Magnetic Materials, 1996, 157-158, 641-642.	1.0	3
195	Magnetic anisotropy of $\text{RCo}_{10}\text{Si}_2$ compounds (R = Y, Gd, Dy, Ho, Er, Tm). Physica B: Condensed Matter, 1996, 228, 214-218.	1.3	7
196	Antiferromagnetic interactions in $\text{Nd}_6\text{Fe}_{12}\text{Ga}_2$ -based compounds. Physica B: Condensed Matter, 1995, 211, 102-104.	1.3	11
197	Electrical characteristics of single, double & surround gate vertical MOSFETs with reduced overlap capacitance. , 0, , .		2
198	CMOS-compatible vertical MOSFETs and logic gates with reduced parasitic capacitance. , 0, , .		2

#	ARTICLE	IF	CITATIONS
199	Catalyst free low temperature direct growth of carbon nanotubes. , 0, , .		2
200	$\text{Bu}_2\text{Sn}(\text{S}\text{Bu})_2$ and $\text{Bu}_3\text{SnE}\text{Bu}$ (E = S or Se) “effective single source precursors for the CVD of SnS and SnSe thermoelectric thin films. Materials Advances, 0, , .	2.6	5
201	Confining the growth of mesoporous silica films into nanospaces: towards surface nanopatterning. Nanoscale Advances, 0, , .	2.2	2